



10N80

Power MOSFET

800 V N-CHANNEL MOSFET

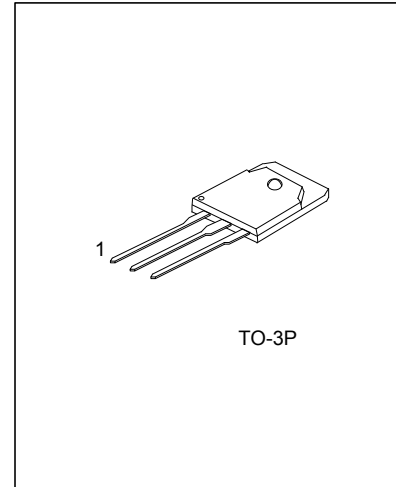
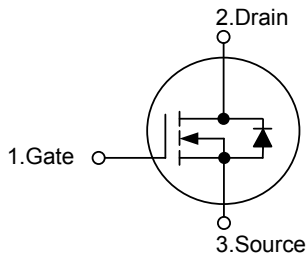
DESCRIPTION

The UTC **10N80** uses UTC's advanced proprietary, planar stripe, DMOS technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * $R_{DS(ON)} = 1.1\Omega$ @ $V_{GS} = 10\text{ V}$
- * Ultra low gate charge (typical 44 nC)
- * Low reverse transfer capacitance ($C_{RSS} =$ typical 15 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



*Pb-free plating product number: 10N80L

ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
10N80-T3P-T	10N80L-T3P-T	TO-3P	G	D	S	Tube

10N80L-T3P-T	(1)Packing Type	(1) T: Tube
	(2)Package Type	(2) T3P: TO-3P
	(3)Lead Plating	(3) L: Lead Free Plating, Blank: Pb/Sn

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	800	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current ($T_C = 25^{\circ}C$)		I_D	10	A
Pulsed Drain Current (Note 1)		I_{DM}	40	A
Avalanche Current (Note 1)		I_{AR}	10	A
Avalanche Energy	Single Pulsed(Note 2)	E_{AS}	920	mJ
	Repetitive(Note 1)	E_{AR}	24	
Peak Diode Recovery dv/dt (Note 3)		dv/dt	4.0	V/ns
Power Dissipation		P_D	240	W
Derate above 25°C			1.92	W/°C
Junction Temperature		T_J	150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction-to- Ambient	θ_{JA}			40	$^\circ\text{C}/\text{W}$
Junction-to-Case	θ_{JC}			0.52	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	800			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=800\text{V}, V_{GS}=0\text{ V}$			10	μA
		$V_{DS}=640\text{V}, T_C=125^\circ\text{C}$			100	
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0\text{ V}, V_{GS}=\pm 30\text{ V}$			± 100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\text{ }\mu\text{A}$, Referenced to 25°C		0.98		mV/ $^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$	3.0		5.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{ V}, I_D=5.0\text{ A}$		0.93	1.1	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$		2150	2800	pF
Output Capacitance	C_{OSS}			180	230	pF
Reverse Transfer Capacitance	C_{RSS}			15	20	pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=400\text{V}, I_D=10.0\text{A},$ $R_G=25\Omega$ (Note 4,5)		50	110	ns
Turn-ON Rise Time	t_R			130	270	
Turn-OFF Delay Time	$t_{D(OFF)}$			90	190	
Turn-OFF Fall-Time	t_F			80	170	
Total Gate Charge	Q_G	$V_{DS}=640\text{V}, V_{GS}=10\text{V},$ $I_D=10.0\text{A}$ (Note 4,5)		45	58	nC
Gate Source Charge	Q_{GS}			13.5		
Gate Drain Charge	Q_{GD}			17		

■ ELECTRICAL CHARACTERISTICS(Cont.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=10.0\text{ A}, V_{GS}=0\text{ V}$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				10.0	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				40.0	
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_F/dt = 100\text{ A/s},$		730		ns
Reverse Recovery Charge	Q_{RR}	$I_S = 10.0\text{ A (Note 4)}$		10.9		nC

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. $L=17.3\text{ mH}$, $I_{AS}=10\text{ A}$, $V_{DD}=50\text{ V}$, $R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$.
3. $I_{SD} \leq 10\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$.
4. Pulse Test: Pulse Width $\leq 300\text{ s}$, Duty Cycle $\leq 2\%$.
5. Independent of operating temperature.

■ TEST CIRCUIT

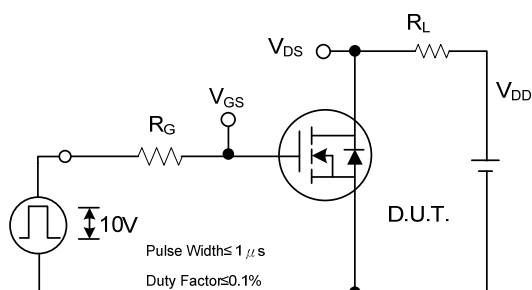


Fig. 2A Switching Test Circuit

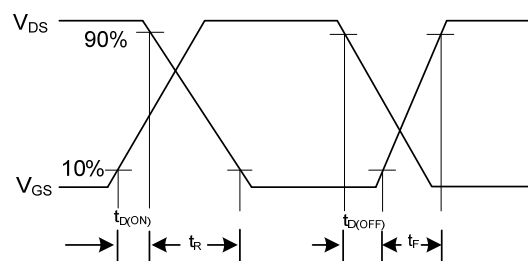


Fig. 2B Switching Waveforms

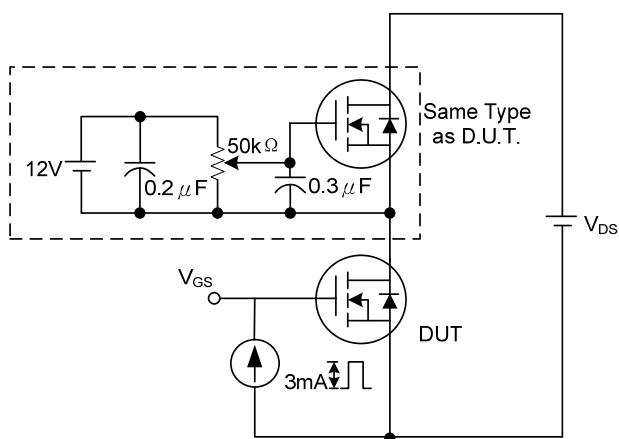


Fig. 3A Gate Charge Test Circuit

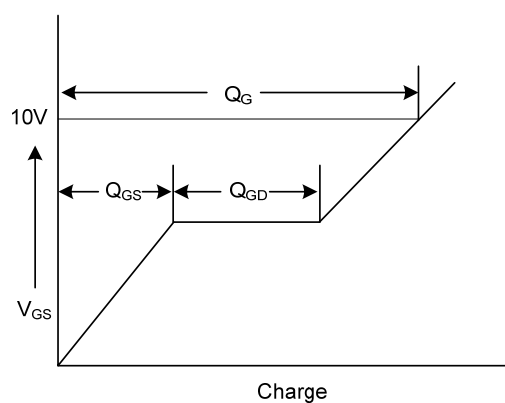


Fig. 3B Gate Charge Waveform

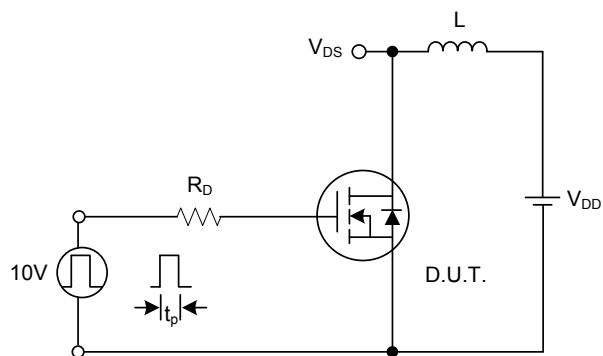


Fig. 4A Unclamped Inductive Switching Test Circuit

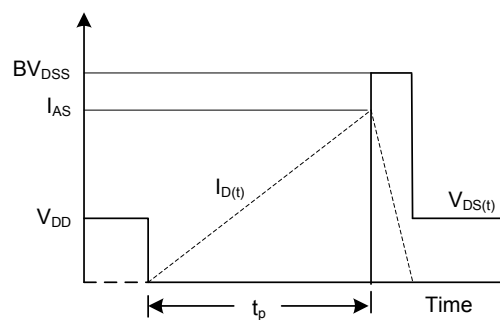


Fig. 4B Unclamped Inductive Switching Waveforms

■ TEST CIRCUIT(Cont.)

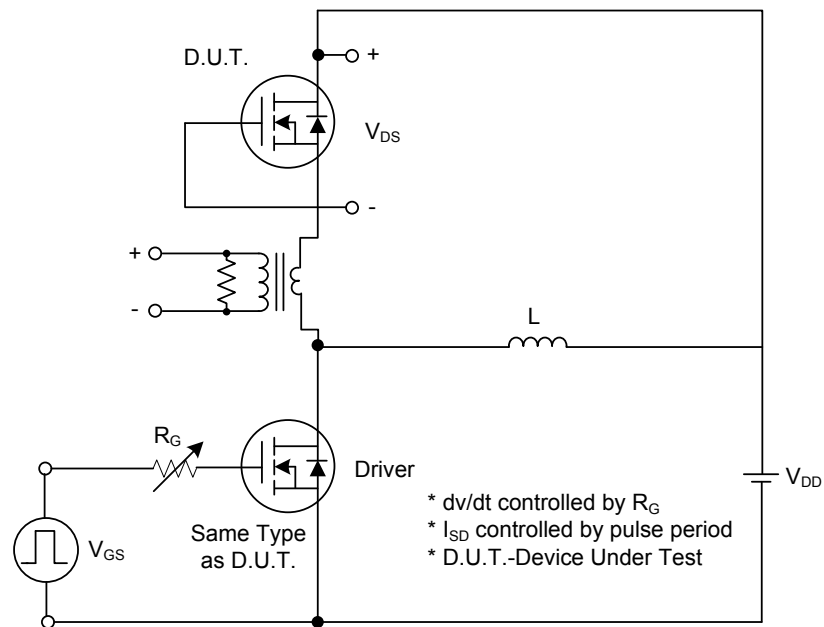
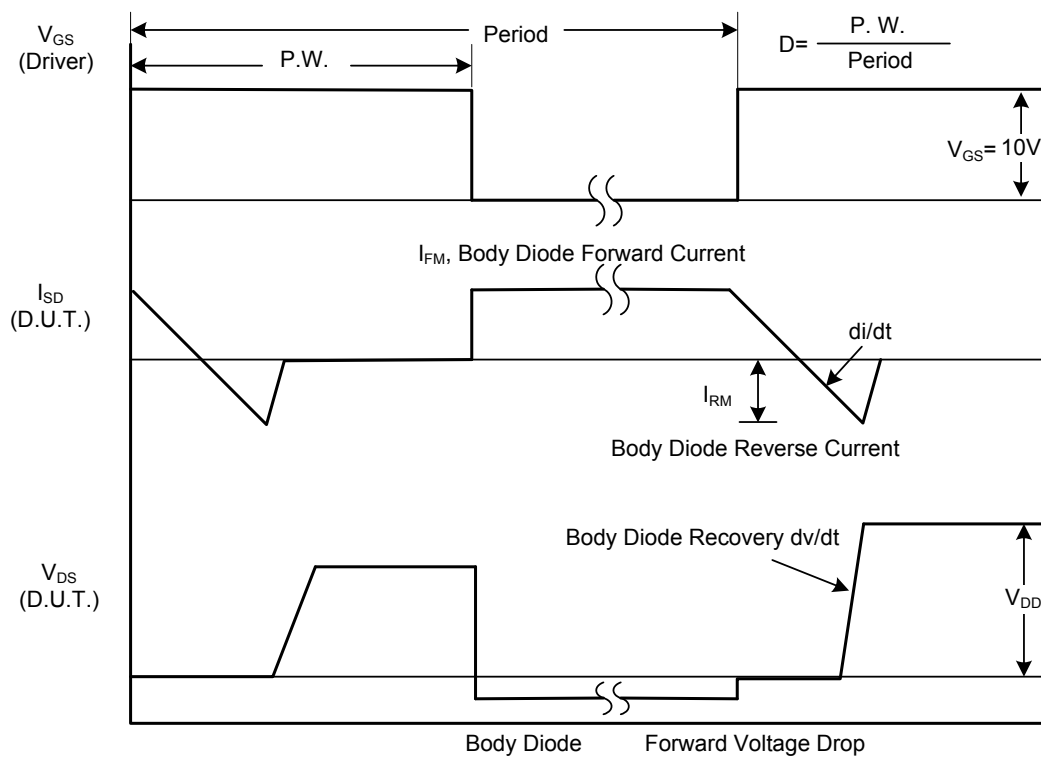
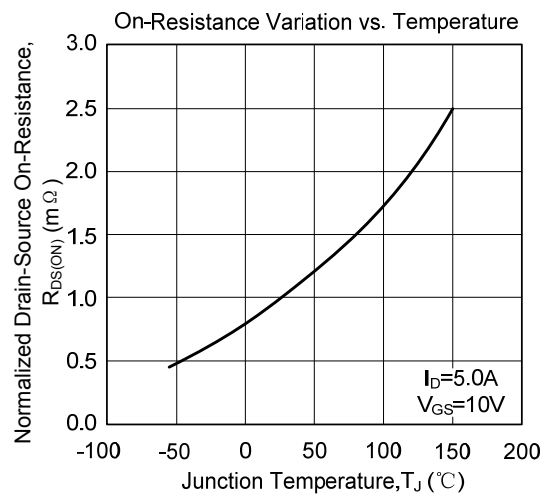
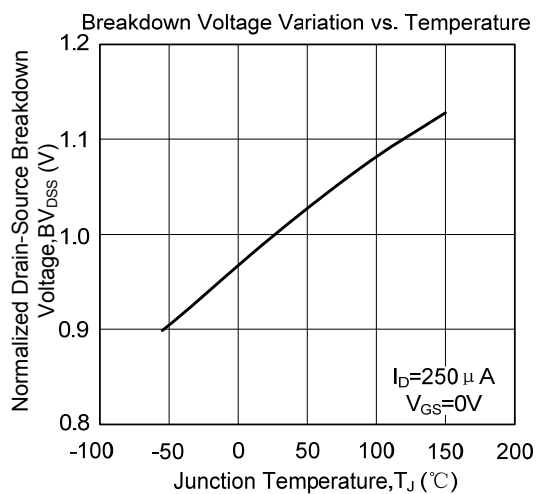
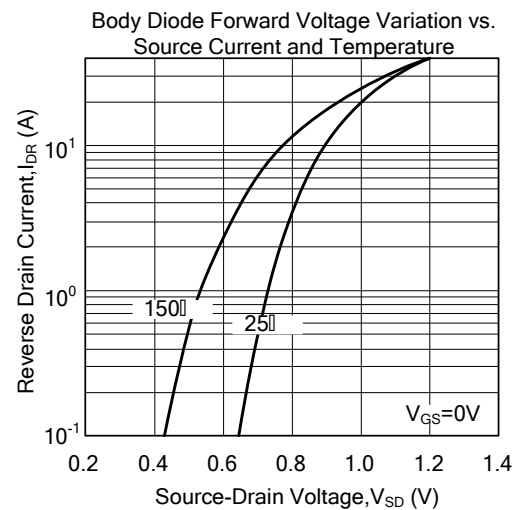
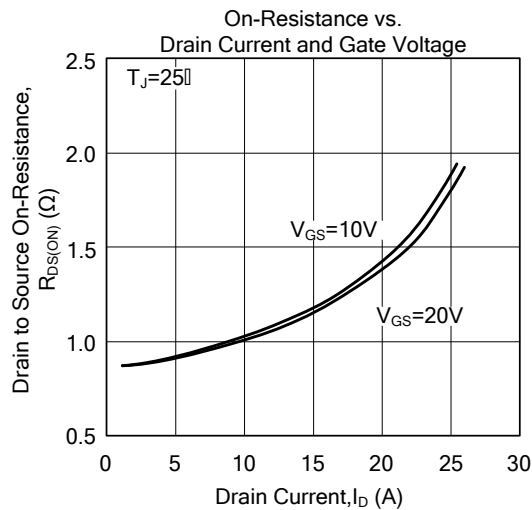
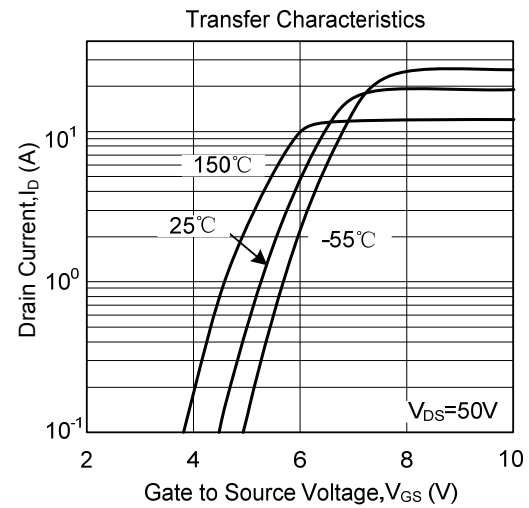
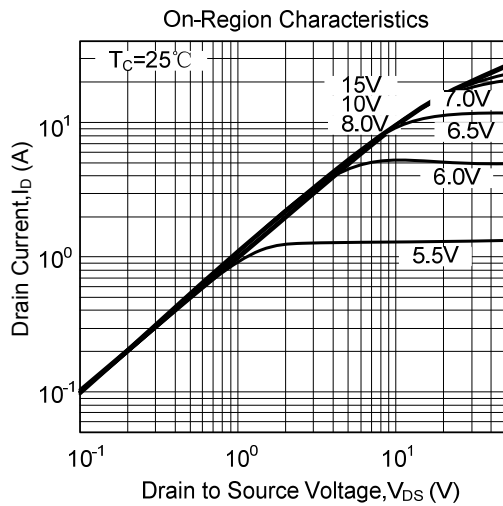


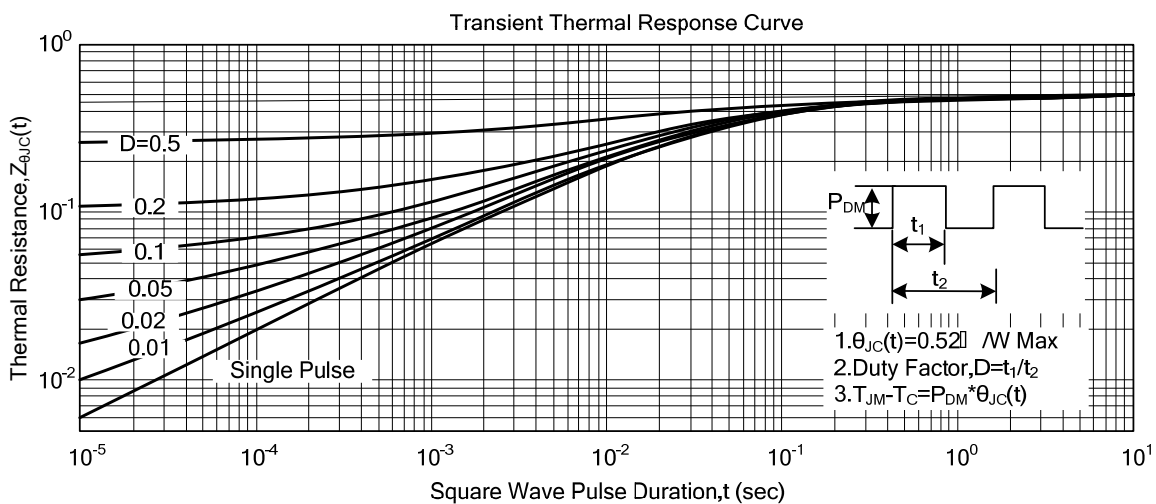
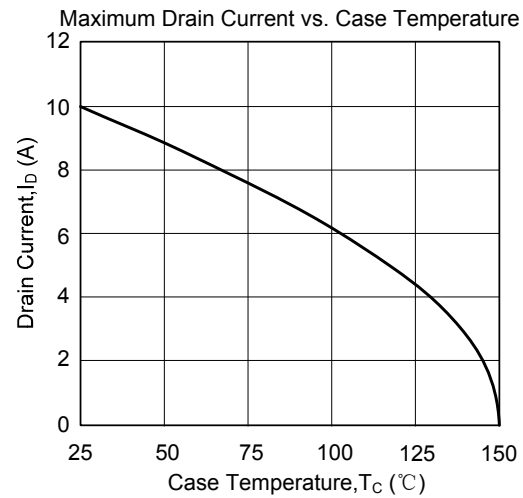
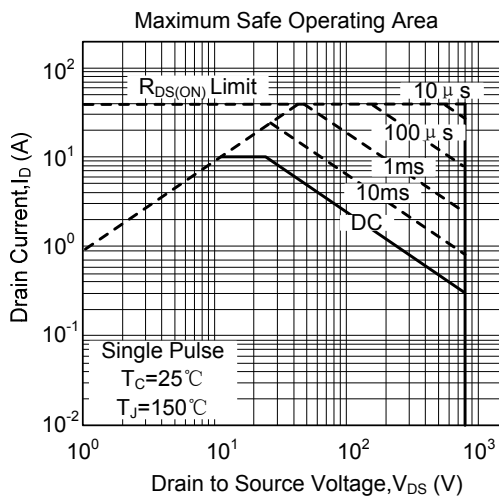
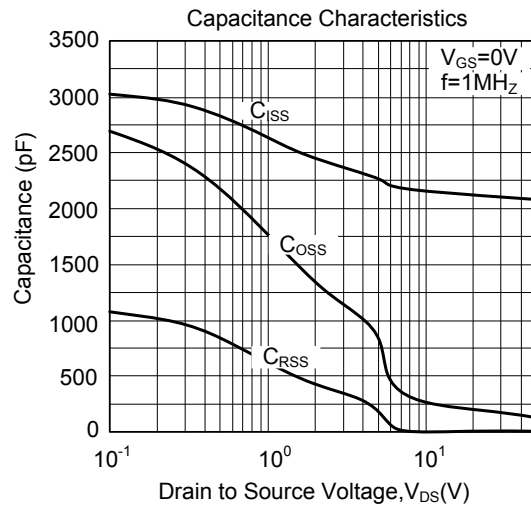
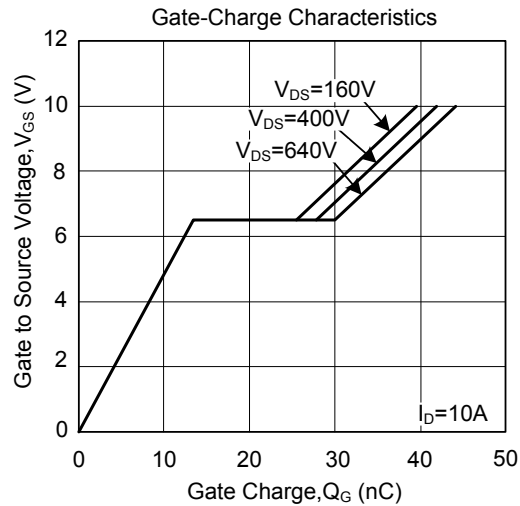
Fig. 1A Peak Diode Recovery dv/dt Test Circuit



■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS



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